

# SILICON TRANSISTOR ARRAY

 $\mu$ PA1434

## NPN SILICON POWER TRANSISTOR ARRAY LOW SPEED SWITCHING USE INDUSTRIAL USE

#### **DESCRIPTION**

The  $\mu$ PA1434 is NPN silicon epitaxial Power Transistor Array that built in 4 circuits designed for driving solenoid, relay, lamp and so on.

#### **FEATURES**

- Easy mount by 0.1 inch of terminal interval.
- High hre. Low Vce(sat).
   hre = 800 to 3200 (at Ic = 0.5 A)
   Vce(sat) = 0.5 V MAX. (at Ic = 2 A)

#### ORDERING INFORMATION

| Part Number | Package    | Quality Grade |  |  |
|-------------|------------|---------------|--|--|
| μPA1434H    | 10 Pin SIP | Standard      |  |  |

Please refer to "Quality grade on NEC Semiconductor Device" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

## ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

| Collector to Base Voltage                       | Vсво               | 60      | V      |  |  |
|---|--------------------|---------|--------|--|--|
| Collector to Emitter Voltage                    | VCEO               | 60      | V      |  |  |
| Emitter to Base Voltage                         | VEBO               | 7       | V      |  |  |
| Collector Current (DC)                          | Ic(DC)             | 3       | A/unit |  |  |
| Collector Current (pulse)                       | C(pulse)*          | 6       | A/unit |  |  |
| Base Current (DC)                               | B(DC)              | 0.6     | A/unit |  |  |
| Total Power Dissipation                         | P <sub>T1</sub> ** | 3.5     | W      |  |  |
| $(T_a = 25  ^{\circ}C)$                         |                    |         |        |  |  |
| Total Power Dissipation                         | P <sub>T2</sub> ** | 28      | W      |  |  |
| $(T_c = 25  ^{\circ}C)$                         |                    |         |        |  |  |
| Junction Temperature                            | Tj                 | 150     | °C     |  |  |
| Storage Temperature                             | Tstg -55           | to +150 | ) °C   |  |  |
| * PW $\leq$ 300 $\mu$ s, Duty Cycle $\leq$ 10 % |                    |         |        |  |  |

PACKAGE DIMENSION
(in millimeters)

26.8 MAX.

26.8 MAX.

1.4 0.6 ± 0.1

2.54

1.2 3 4 5 6 7 8 910

CONNECTION DIAGRAM

PIN NO.

2, 4, 6, 8: Base (B)
3, 5, 7, 9: Collector (C)
1, 10: Emitter (E)

The information in this document is subject to change without notice.

\*\* 4 Circuits

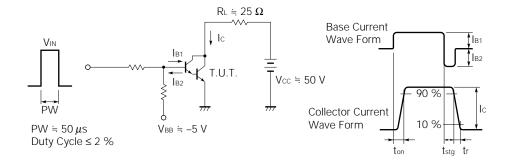


# ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

| CHARACTERISTIC               | SYMBOL                 | MIN. | TYP. | MAX. | UNIT | TEST CONDITIONS  |
|------------------------------|------------------------|------|------|------|------|--|
| Collector Leakage Current    | Ісво                   |      |      | 10   | μΑ   | Vcb = 60 V, IE = 0   |
| Emitter Leakage Current      | Ієво                   |      |      | 10   | μΑ   | V <sub>EB</sub> = 5 V, I <sub>C</sub> = 0                                    |
| DC Current Gain              | h <sub>FE1</sub> *     | 800  |      | 3200 | _    | Vce = 5 V, Ic = 0.5 A  |
| DC Current Gain              | h <sub>FE2</sub> *     | 500  |      |      | _    | Vce = 5 V, Ic = 3 A  |
| Collector Saturation Voltage | V <sub>CE(sat)</sub> * |      |      | 0.5  | V    | Ic = 2 A, I <sub>B</sub> = 20 mA   |
| Base Saturation Voltage      | V <sub>BE(sat)</sub> * |      |      | 1.2  | V    | Ic = 2 A, I <sub>B</sub> = 20 mA   |
| Turn On Time                 | ton                    |      | 1    |      | μs   | Ic = 2 A   |
| Storage Time                 | tstg                   |      | 3    |      | μs   | $I_{B1} = -I_{B2} = 10 \text{ mA}$ $V_{CC} = 50 \text{ V, } R_L = 25 \Omega$ |
| Fall Time                    | tf                     |      | 1.5  |      | μs   | See test circuit   |

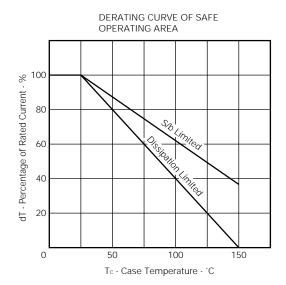
<sup>\*</sup> PW  $\leq$  350  $\mu$ s, Duty Cycle  $\leq$  2 % /pulsed

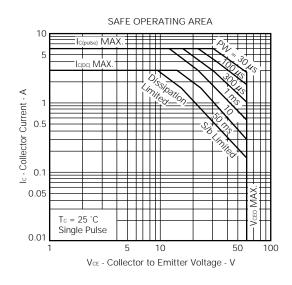
## **SWITCHING TIME TEST CIRCUIT**

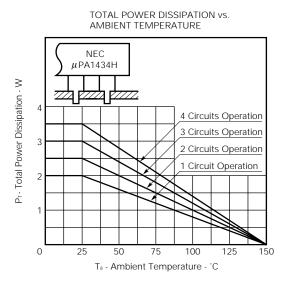


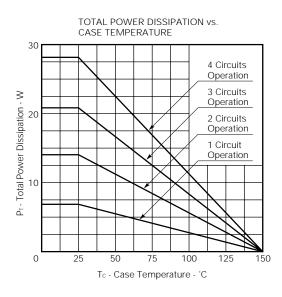


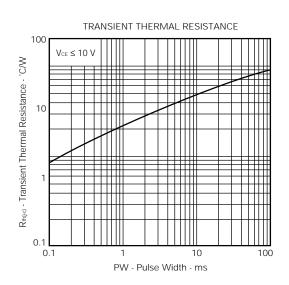
### TYPICAL CHARACTERISTICS (Ta = 25 °C)

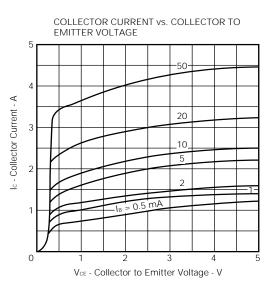


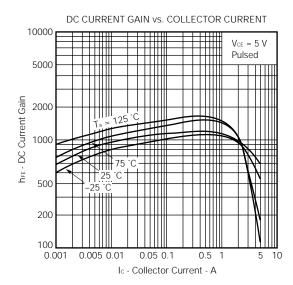


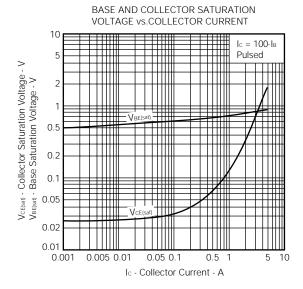














# REFERENCE

| Document Name  | Document No. |
|--|--------------|
| NEC semiconductor device reliability/quality control system. | TEI-1202     |
| Quality grade on NEC semiconductor devices.                  | IEI-1209     |
| Semiconductor device mounting technology manual.             | IEI-1207     |
| Semiconductor device package manual.                         | IEI-1213     |
| Guide to quality assurance for semiconductor devices.        | MEI-1202     |
| Semiconductor selection guide.                               | MF-1134      |

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